

What is claimed is:

1. An optical transmission module comprising:

a driver IC chip which drives a semiconductor laser device;

a first insulation plate which is placed adjacent to the driver IC chip and has the semiconductor laser device mounted thereon;

a coupling optical component which is place adjacent to the first insulation plate and is used to emit an optical signal from the semiconductor laser device into an optical fiber; and

a second insulation plate which is placed adjacent to the first insulation plate and has a thin film inductor element and a thin film resistor element mounted thereon;

wherein the driver IC chip, the first insulation plate, the coupling optical component, and the second insulation plate are contained in a package; and

wherein the first insulation plate and the second insulation plate are connected by using a bonding wire or ribbon so that a bias current is supplied to the semiconductor laser device via the thin film inductor element and the thin film resistor element which are connected in parallel.

2. An optical transmission module according to claim 1 wherein a terminal of the driver IC chip is connected

with an electrode on the first insulation plate by using a bonding wire or ribbon.

3. An optical transmission module according to claim 1 wherein a resonant frequency in a resonant circuit composed of grounding capacitance of the thin film inductor element on the second insulation plate and an inductance of the bonding wire is not lower than 8 GHz.

4. An optical transmission module according to claim 1 wherein the driver IC chip is a current drive type.

5. An optical transmission module according to claim 2 wherein the driver IC chip is a current drive type.

6. An optical transmission module wherein a bias current is supplied to a semiconductor laser device via a thin film inductor element and a thin film resistor element which are connected in parallel.

7. An optical transmission module according to claim 6 wherein a first insulation plate having the semiconductor laser device mounted thereon and a second insulation plate having the thin film inductor element and the thin film resistor element formed thereon are respectively formed as separate insulation plates and an electrode formed on the first insulation plate is connected via a bonding wire or ribbon with one end pad of the thin film inductor element and the thin film resistor element which are connected in parallel.

8. An optical transmission module according to claim

7 wherein a resonant frequency in a resonant circuit composed of grounding capacitance of the thin film inductor element on the second insulation plate and an inductance of the bonding wire is not lower than 8 GHz.

9. An optical transmission module according to claim 7 wherein a driver IC chip to drive the semiconductor laser device is placed adjacent to the first insulation plate and a terminal of the driver IC chip is connected with an electrode on the first insulation plate by using bonding a wire or ribbon.

10. An optical transmission module according to claim 9 wherein the driver IC chip is a current drive type.